

Form PTO-1449
(Rev. 8-83)U.S. Department of Commerce
Patent and Trademark Office

Attorney Docket No. 0756-2222

Serial No. Not Yet Assigned

INFORMATION DISCLOSURE STATEMENT

(Use several sheets if necessary)

Applicant: Shunpei YAMAZAKI et al.

Filing Date: October 31, 2000

Group: 2823

U.S. PATENT DOCUMENTS

Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date (if appropriate)
AKS	5,403,772	04/04/95	Zhang et al			
AKS	5,426,064	06/20/95	Zhang et al			
AKS	5,481,121	01/02/96	Zhang et al			
AKS	5,488,000	01/30/96	Zhang et al			
AKS	5,492,843	02/20/96	Adachi et al			
AKS	5,501,989	03/26/96	Takayama et al			
AKS	5,508,533	04/16/96	Takemura			
AKS	5,529,937	06/25/96	Zhang et al			
AKS	5,534,716	07/09/96	Takemura			
AKS	5,543,352	08/06/96	Ohtani et al			
AKS	5,563,426	10/08/96	Zhang et al			
AKS	5,569,610	10/29/96	Zhang et al			
AKS	5,569,936	10/29/96	Zhang et al			
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AKS	5,585,291	12/17/96	Ohtani et al			
AKS	5,589,694	12/31/96	Takayama et al			
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AKS	5,639,698	06/17/97	Yamazaki			
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09/16/99, 466

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U.S. PATENT DOCUMENTS

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AKS	5,595,923	01/21/97	Zhang et al			
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AKS	5,604,360	02/18/97	Zhang et al			
AKS	5,605,846	02/25/97	Ohtani et al			
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AKS	5,624,851	04/29/97	Takayama et al			
AKS	5,637,515	06/10/97	Takemura			
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AKS	Kawazu, "Initial Stage of the Interfacial Reaction between Nickel and Hydrogenated Amorphous Silicon" Japanese Journal of Applied Physics, Vol. 29, No. 4, April 1990, pgs. 729-738.
AKS	Wolf et al., "Silicon Processing for the VLSI Era", Vol. 1, pgs 550-551, 1986.

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Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date (if appropriate)
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ACS	5,766,977	06/16/98	Yamazaki	438	151	
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Document Number	Date	Country	Class	Subclass	Translation Yes No	

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09/699,466

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AKS	1-187874	07/27/89	Japan			Abstract	
AKS	2-275641	09/11/90	Japan			Abstract	

09/699,466

AKS	61-63107	04/01/86	Japan			Abstract	
AKS	3-280420 (Japanese & English)	12/11/91	Japan			Full	
AKS.	5-82442	04/02/93	Japan			Abstract	
AKS	7-16134	06/23/95	Japan			Abstract	
AKS	2-140915	05/20/90	Japan			Full	
AKS	1-206632	08/18/89	Japan			Abstract	
AKS	52-99348	11/93	Japan			Abstract	
AKS	0178447	09/10/84	European			Full	
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